

# XP01878

## Silicon N-channel MOSFET

For switching

### ■ Features

- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half

### ■ Basic Part Number

- 2SK3539 × 2

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

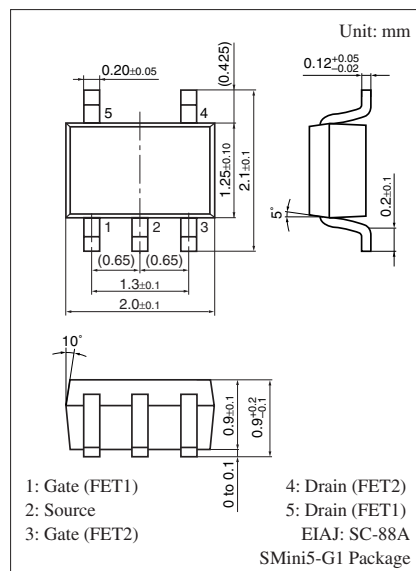
Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	$V_{\text{DSS}}$	50	V
Gate-source voltage (Drain open)	$V_{\text{GSO}}$	$\pm 7$	V
Drain current	$I_{\text{D}}$	100	mA
Peak drain current	$I_{\text{DP}}$	200	mA
Total power dissipation	$P_{\text{T}}$	150	mW
Channel temperature	$T_{\text{ch}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +125	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source surrender voltage	$V_{\text{DSS}}$	$I_{\text{D}} = 10 \mu\text{A}$ , $V_{\text{GS}} = 0$	50			V
Drain-source cutoff current	$I_{\text{DSS}}$	$V_{\text{DS}} = 50 \text{ V}$ , $V_{\text{GS}} = 0$			1.0	$\mu\text{A}$
Gate-source cutoff current	$I_{\text{GSS}}$	$V_{\text{GS}} = \pm 7 \text{ V}$ , $V_{\text{DS}} = 0$			$\pm 5$	$\mu\text{A}$
Gate threshold voltage	$V_{\text{th}}$	$I_{\text{D}} = 1 \mu\text{A}$ , $V_{\text{DS}} = 3 \text{ V}$	0.9	1.2	1.5	V
Drain-source ON resistance	$R_{\text{DS(on)}}$	$I_{\text{D}} = 10 \text{ mA}$ , $V_{\text{GS}} = 2.5 \text{ V}$		8	15	$\Omega$
		$I_{\text{D}} = 10 \text{ mA}$ , $V_{\text{GS}} = 4.0 \text{ V}$		6	12	
Forward transfer admittance	$ Y_{\text{fs}} $	$I_{\text{D}} = 10 \text{ mA}$ , $V_{\text{DS}} = 4.0 \text{ V}$	20	60		mS
Short-circuit forward transfer capacitance (Common source)	$C_{\text{iss}}$	$V_{\text{DS}} = 3 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$ , $f = 1 \text{ MHz}$		12		pF
Short-circuit output capacitance (Common source)	$C_{\text{oss}}$			7		pF
Reverse transfer capacitance (Common source)	$C_{\text{rss}}$			3		pF
Turn-on time *	$t_{\text{on}}$	$V_{\text{DD}} = 3 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$ to $3 \text{ V}$ , $R_{\text{L}} = 470 \Omega$		200		ns
Turn-off time *	$t_{\text{off}}$	$V_{\text{DD}} = 3 \text{ V}$ , $V_{\text{GS}} = 3 \text{ V}$ to $0 \text{ V}$ , $R_{\text{L}} = 470 \Omega$		200		ns

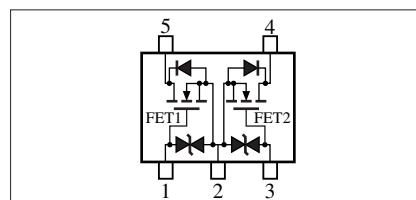
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

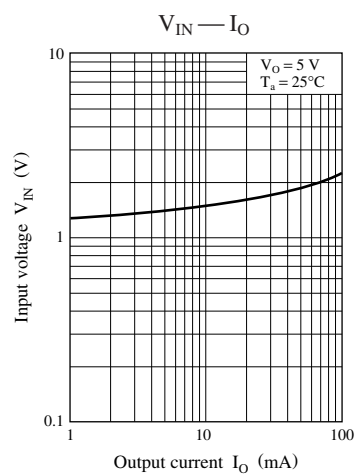
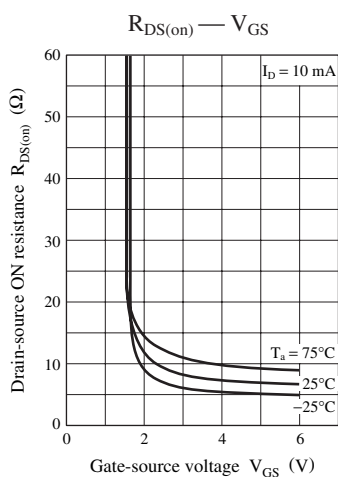
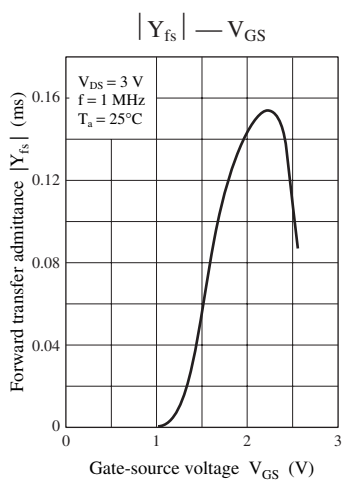
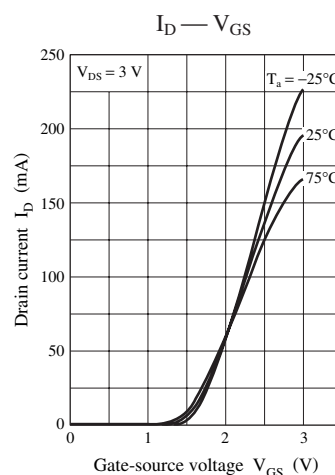
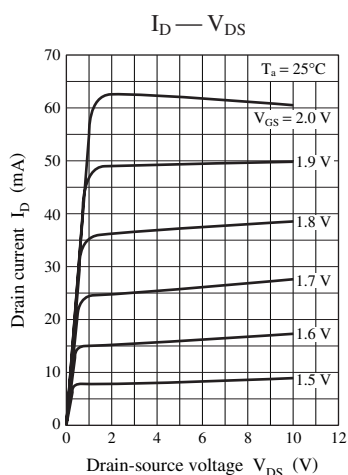
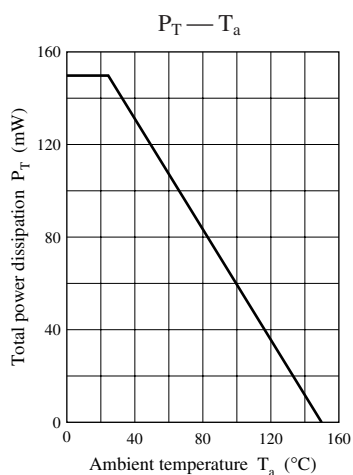
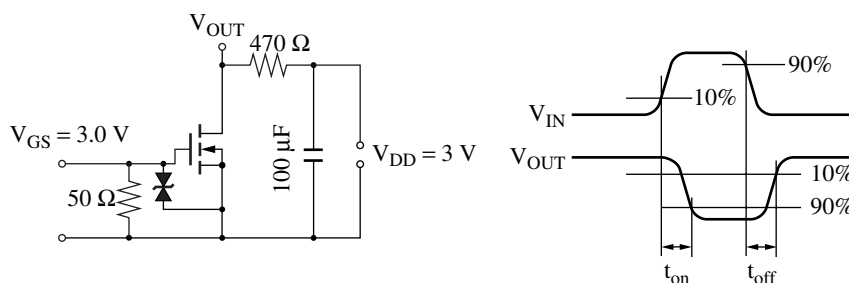
2. \*: Refer to  $t_{\text{on}}$ ,  $t_{\text{off}}$  test circuit (next page)



Marking Symbol: AL

Internal Connection



$t_{on}$ ,  $t_{off}$  test circuit

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